Supporting Information

Absolute Energy Levels in Nanodiamonds of Different Origins and Surface Chemistries

Daria Miliaieva,^{*a,e} Aurelien Sokeng Djoumessi,^{b,c} Jan Cermak,^a Katerina Kolarova,^a Maximilian Schaal,^d Felix Otto,^d Ekaterina Shagieva,^a Olexandr Romanyuk,^a Jiri Pangrac,^a Jaroslav Kulicek,^e Vojtech Nádaždy,^{f,g} Stepan Stehlik^{a,h} Alexander Kromka,^a Harald Hoppe^{b,c} Bohuslav Rezek^e

^aInstitute of Physics, Czech Academy of Sciences, Na Slovance 1999/2, 182 21 Prague 8, Czech Republic

^bCenter for Energy and Environmental Chemistry Jena (CEEC Jena), Friedrich Schiller University Jena, Philosophenweg 7a, 07743 Jena, Germany

^cLaboratory of Organic and Macromolecular Chemistry (IOMC), Friedrich Schiller University Jena, Humboldstrasse 10, 07743 Jena, Germany

^dInstitute of Solid State Physics, Friedrich Schiller University Jena, Helmholtzweg 5, 07743 Jena, Germany

^eFaculty of Electrical Engineering, Czech Technical University in Prague, 166 27 Prague, Czech Republic

^fInstitute of Physics, Slovak Academy of Sciences, Dúbravská cesta 9, 845 11 Bratislava, Slovak RepublicRepublic

^gCentre for Advanced Material Application, Slovak Academy of Sciences, Dúbravská cesta 9, 845 11 Bratislava, Slovak Republic

^hNew Technologies – Research Centre, University of West Bohemia, Univerzitní 8, 306 14, Pilsen, Czech Republic

Energy-Resolved Electrochemical Impedance Spectroscopy (ER-EIS)

ER-EIS is a novel technique originally used to map the electronic density of states (DOS) in organic semiconductors [V. Nadazdy, F. Schauer, K. Gmucova, Appl. Phys. Lett. 2014, 105, 142109]. This method measures the impedance of the semiconductor film/electrolyte system at a frequency, where the redox reaction dominates and other electrochemical processes are eliminated. The redox reaction then determines the chargetransfer resistance, R_{ct} , which is evaluated from the real part of the impedance. The DOS function g(*E*) can be then determined directly from the obtained $R_{ct}(E_F)$ function, where the Fermi energy $E_F = eU$ is given by the applied voltage *U*:

$$g(E_F) = \frac{1}{e^2 k_{et}[A] SR_{ct}(E_F)} ,$$

where *e* is the elemental charge, k_{et} is the charge-transfer coefficient (~10²⁴ cm⁴s⁻¹), [*A*] is the concentration of the redox species dissolved in the solvent (6x10¹⁹ cm⁻³), and *S* is the area of the working electrode [F. Schauer, V. Nadazdy, K. Gmucova, J. Appl. Phys. 2018, 123, 161590]. By sweeping the applied voltage *U* it is possible to map the DOS in a wide energy range.

Experimentally, ER-EIS measurements were performed in electrochemical microcells with a volume of about \approx 200 µL, which were formed by glueing the set of plastic cones on nanodiamond layers spin-coated on the ITO substrate. A three-electrode configuration was used, with the nanodiamond layer as the working electrode, Ag/AgCl as the reference electrode and a platinum wire as the auxiliary electrode. The applied bias voltage adjusted relative to the Ag/AgCl electrode was recalculated to the energy scale, assuming the Ag/AgCl energy vs. vacuum value of – 4.66 eV. The active working electrode area *S* was 12 mm². The solution of 0.1 m

TBAPF₆ in anhydrous acetonitrile was used as the supporting electrolyte. To avoid intercalation of ions the measurement of the whole spectrum is performed in two steps, always in a new electrochemical cell, with one measurement being used to obtain the branch for the hole-transporting states and one for the electron-transporting states. [V. Nadazdy, F. Schauer, K. Gmucova, Appl. Phys. Lett. 2014, 105, 142109; H. Bässler, D. Kroh, F. Schauer, V. Nádaždy, A. Köhler, Adv. Funct. Mater. 31 (2021) 2007738]. The impedance/gain-phase analyzer (Model 1260, Solartron Analytical, UK) was employed in connection with a homemade potentiostat in the standard three-electrode configuration. The AC signal frequency and the RMS value of AC voltage were set to 0.5 Hz and 100 mV, respectively. The measurements were performed in a glove box with a protective N₂ atmosphere (oxygen and moisture below 20 ppm and 2 ppm, respectively).







Figure S2. a) DND-ar fractionation confirmed by DLS b) UV-VIS absorbance of DND-ar fractions c) Tauc plots of DND-ar fractions with tangents for energy band gap (E_g) determination. This experiment demonstrates that a DND-ar fraction of 70 - 700 nm causes pronounced scattering, which contributes to the apparent E_g = 5.1 eV. This fraction results in turbidity of the DNDs colloids as can be seen from the inset photos.



Figure S3. ND absorbance spectra.

Figure S4 shows the spectra of the C 1s core levels for a) HPHT, b) DND, and c) the normalized spectra from the Au substrates. Spectra positions were calibrated with respect to the position of the Au 4f^{7/2} peak maxima at 84 eV. The C 1s peak position of the adventitious carbon on the Au reference substrate (adv. C/Au) lies at 285 eV. The positions of the C 1s peaks of the ND samples depend on the electronic properties of materials and evident that photoemitted electrons in HPHT ND-H have ~ 1.6 eV less core level electrons binding energy than in DNDs and oxidised HPHTs.



Figure S4. C 1s spectra measured on a) HPHT and b) DND differently terminated samples. c) Au 4f spectra from reference Au substrate and from overlayer of NDs on Au. Shifts of C 1s positions are related to the different core C 1s binding energy of electrons.

Table S1 shows values of the full width at half maximum (FWHM) of sp³ C 1s peaks obtained by XPS. The FWHM of the HPHT ND samples (0.8 - 1.1 eV) is more than twice as narrower compared to the FWHM of the DND samples (2.0 - 2.5 eV). It corroborates the more defective nature of DNDs compared to HPHTs revealed by Raman spectroscopy.

Table S1.			
The full width at half maximum (FWHM) of C 1s XPS peak in NDs.			
	FWHM, eV		FWHM, eV
	(sp³)		(sp³)
HPHT ND-ar	1.1	DND-ar	2.5
HPHT ND-O	0.9	DND-O	2.0
HPHT ND-H	0.8	DND-H	2.5



Figure S5. Determination of the UPS binding energy cut-off of HPHT ND-H before and after heating at 250 °C for 1h. The cut-off indicates the VBM position is 0.3 eV upshifted relative to Fermi level (at 0 eV binding energy) in ambient conditions compared to the HPHT ND-H surface without adsorbates due to band bending.